

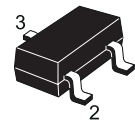
## SMALL SIGNAL NPN TRANSISTOR

Type	Marking
BCX19	U1

- SILICON EPITAXIAL PLANAR NPN TRANSISTOR
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPE IS BCX17

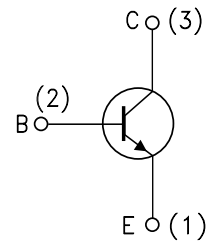
### APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



SOT-23

### INTERNAL SCHEMATIC DIAGRAM



DS10130

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	50	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	45	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	5	V
$I_C$	Collector Current	0.5	A
$I_{CM}$	Collector Peak Current	1	A
$P_{tot}$	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	mW
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

## BCX19

### THERMAL DATA

$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	500	$^{\circ}\text{C}/\text{W}$
---------------	-------------------------------------	-----	-----	-----------------------------

• Device mounted on a PCB area of  $1\text{ cm}^2$ .

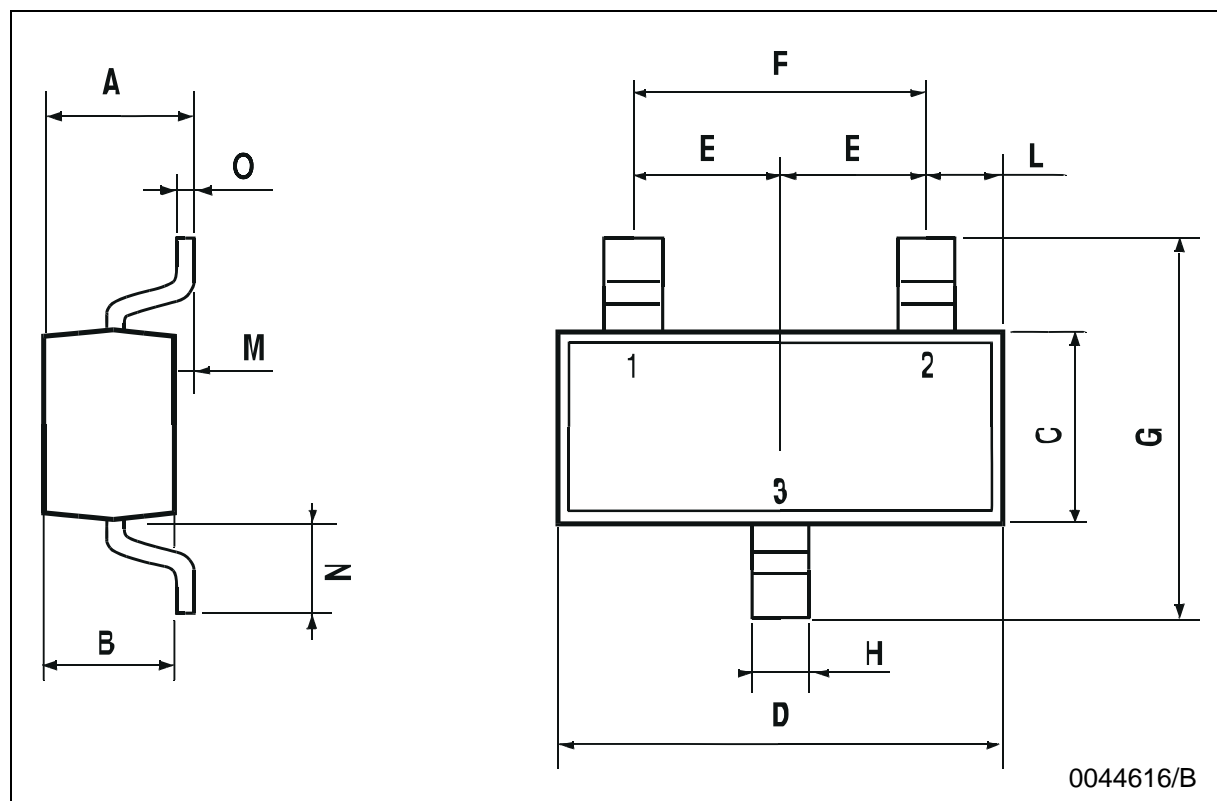
### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 20\text{ V}$ $V_{CB} = 20\text{ V}$ $T_C = 150\text{ }^{\circ}\text{C}$			100 5	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5\text{ V}$			100	nA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_E = 0$ )	$I_C = 10\text{ }\mu\text{A}$	50			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 10\text{ mA}$	45			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = 10\text{ }\mu\text{A}$	5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 500\text{ mA}$ $I_B = 50\text{ mA}$			0.62	V
$V_{BE(on)}^*$	Base-Emitter On Voltage	$I_C = 500\text{ mA}$ $V_{CE} = 1\text{ V}$			1.2	V
$h_{FE}^*$	DC Current Gain	$I_C = 100\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 300\text{ mA}$ $V_{CE} = 1\text{ V}$ $I_C = 500\text{ mA}$ $V_{CE} = 1\text{ V}$	100 70 40		600	
$f_T$	Transition Frequency	$I_C = 10\text{ mA}$ $V_{CE} = 5\text{ V}$ $f = 100\text{ MHz}$	100			MHz
$C_{CBO}$	Collector-Base Capacitance	$I_E = 0\text{ mA}$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$		5		pF

\* Pulsed: Pulse duration =  $300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

## SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.85		1.1	33.4		43.3
B	0.65		0.95	25.6		37.4
C	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
H	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
M	0		0.1	0		3.9
N	0.3		0.65	11.8		25.6
O	0.09		0.17	3.5		6.7



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2002 STMicroelectronics – Printed in Italy – All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>